

# **ISC Silicon NPN Power Transistor**

2SD1365

## **DESCRIPTION**

- · High Collector-Base Voltage
  - : V<sub>(BR)CBO</sub>= 800V(Min)
- · Low Collector Saturation Voltage-
  - :  $V_{CE(sat)} = 1.5V(Max) @ I_C = 2A$
- · High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

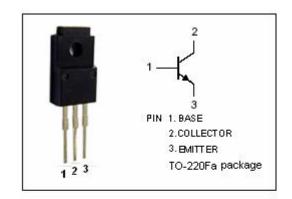


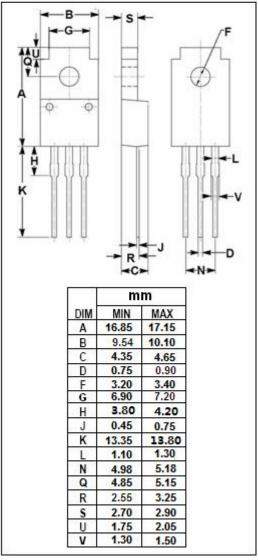
### **APPLICATIONS**

- · Switching regulators
- Motor control systems.
- · Power amplifier.



SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	800	V	
Vceo	Collector-Emitter Voltage	500	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	3	Α	
Ісм	Collector Current-Peak	5	А	
Pc	Collector Power Dissipation @T <sub>a</sub> =25°C	1.5	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	40		
TJ	Junction Temperature	150	$^{\circ}\!\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature -55~150		$^{\circ}$	







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### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

10-20 C unless outerwise specimen									
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	500			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2.0A; I <sub>B</sub> = 0.4A			1.5	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2.0A; I <sub>B</sub> = 0.4A			2.0	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V ; I <sub>E</sub> = 0			10	μ <b>А</b>			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ <b>Α</b>			
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 5mA; V <sub>CE</sub> = 5V	10						
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 5V	20		40				
fτ	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.5A; V <sub>CE</sub> = 10V		7		MHz			
Switching Times									
t <sub>on</sub>	Turn-on Time				1.0	μ <b>S</b>			
ts	Storage Time	I <sub>C</sub> = 2.0A; I <sub>B1</sub> = -I <sub>B2</sub> = 0.4A; V <sub>CC</sub> = 250V			4.0	μ <b>S</b>			
tf	Fall Time				1.0	μ <b>s</b>			

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